

DOCKET NO.: 211147US99



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: : GROUP ART UNIT: 2826

AROON TUNGARE ET AL :

SERIAL NO.: 09/903,784 : EXAMINER: ERDEM

FILED: JULY 13, 2001 :

FOR: STRUCTURE AND METHOD FOR FABRICATING SEMICONDUCTOR
STRUCTURES AND DEVICES UTILIZING PIEZOELECTRIC MATERIALS

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10/ A Hach.
Andlt A
3/6 103*

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Official Action dated August 14, 2002, Applicants respectfully
request reconsideration in view of the following amendment and remarks.

IN THE CLAIMS

Please cancel Claims 1-54.

Please add new Claims 55-90 as follows.

A1 *Guener 653* --55. A semiconductor structure comprising:
Sakura 320 a monocrystalline silicon substrate;
(single crystal perovskite) an amorphous oxide material overlying the monocrystalline silicon substrate;
Kiralyalli 238 a monocrystalline perovskite oxide material overlying the amorphous oxide
(interfacial oxide) material; and
7.1.2 a monocrystalline compound semiconductor material overlying the
monocrystalline perovskite oxide material,

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Takayama
Yero
piezoelectric
(thick)
(compound)
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